

Notice of Allowability	Application No.	Applicant(s)
	10/603,823	TAKENAKA, SATOSHI
	Examiner Hsien-Ming Lee	Art Unit 2823

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1. This communication is responsive to 2/24/04.
2. The allowed claim(s) is/are 1-6.
3. The drawings filed on 26 June 2003 are accepted by the Examiner.
4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) All b) Some* c) None of the:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. 09/524,275.
 3. Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

* Certified copies not received: _____.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.
THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.

5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.
6. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.
 - (a) including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached
 - 1) hereto or 2) to Paper No./Mail Date _____.
 - (b) including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date _____.
7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

Attachment(s)

1. Notice of References Cited (PTO-892)
2. Notice of Draftsperson's Patent Drawing Review (PTO-948)
3. Information Disclosure Statements (PTO-1449 or PTO/SB/08),
Paper No./Mail Date _____
4. Examiner's Comment Regarding Requirement for Deposit
of Biological Material
5. Notice of Informal Patent Application (PTO-152)
6. Interview Summary (PTO-413),
Paper No./Mail Date _____
7. Examiner's Amendment/Comment
8. Examiner's Statement of Reasons for Allowance
9. Other _____.

DETAILED ACTION

Remarks

1. The objection to claims 1-6 is withdrawn.

Examiner's Amendment

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

3. The application has been amended as follows:

In specification, page 12, at line 3, replace “Fig.13” with -- Fig.3 --.

Allowable Subject Matter

4. Claims 1-6 are allowed.
5. The following is an examiner's statement of reasons for allowance:

The prior art of record, Nishimura et al. to US 6,462,802, teaches a method of producing an active matrix substrate, comprising:

- forming a semiconductor film 401 used to form the TFT, and then forming a gate insulating film 106 used to form the TFT (Fig.4A);
- forming a conductive film 107 used to form a gate electrode of the TFT transistor and then patterning the conductive film 107 so as to form the gate electrode (Fig.4B);
- selectively introducing an impurity into the semiconductor film 401 to form source and drain regions 109 of the TFT (Fig.4E);

- forming an interlayer insulating film 110 in a layer on the surface of the gate electrode (Fig. 8);
- forming a contact hole, for connection to the TFT, in the interlayer insulating film 110.

In contrast, Nishimura et al. neither teach or suggest *simultaneously* forming the semiconductor film *for film quality evaluation* in a region to be used as the quality evaluation region; *simultaneously* forming a gate insulating film in the region to be used as the film *quality evaluation region*; *simultaneously* removing the conductive film from the *film quality evaluation region*; *simultaneously* introducing the impurity also into the semiconductor film for film quality evaluation via the gate insulating film *in the evaluation region*; *simultaneously* forming the interlayer insulating film in the *evaluation region*, in a layer on the surface of the gate insulating film in the evaluation region; and *simultaneously* forming, in the *film quality evaluation region*, the opening in the interlayer insulating film in the *evaluation region* and in the gate insulating film in the *evaluation region*.

In the examiner's opinion, it would not have been obvious to one of the ordinary skill in the art, at the time of the invention was made, to modify prior-art's method to arrive the instant invention, especially the aforementioned patentably distinct limitations.

6. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

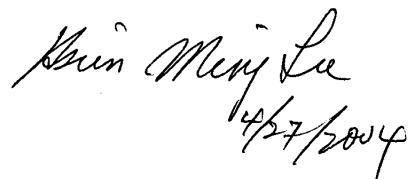
7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hsien-Ming Lee whose telephone number is 571-272-1863. The examiner can normally be reached on M-F (9:00 ~ 5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hsien-Ming Lee
Examiner
Art Unit 2823

April 27, 2004


4/27/2004